

Remarks/Arguments

Reconsideration of this application is requested.

Claim Status

Claims 1-20 are presented. Claims 7-10, 14, 17 and 20, which are withdrawn from consideration as a result of a previous restriction requirement and election, are canceled without prejudice. Claim 2 is also canceled, without prejudice, and claims 1 and 11 are amended. Accordingly, claims 1, 3-6, 11-13, 15, 16, 18 and 19 are now pending.

Claim Rejections – 35 USC 102(e) – Yamaguchi

Claims 1-6, 11-13, 15, 16, 18 and 19 are rejected under 35 USC 102(e) as anticipated by Yamaguchi.

Although Yamaguchi claims priority in JP 2002-240778, filed on August 21, 2002, under 35 USC 102(e), Yamaguchi is effective as prior art only as of its U.S. filing date of August 11, 2003. The present application claims priority in JP 2003-073925, filed on March 18, 2003, which precedes the effective prior art date of Yamaguchi. Thus, Yamaguchi can be removed as a reference by filing a verified English translation of the certified copy of JP 2003-073925. See MPEP 201.15. Accordingly, a verified English translation of the certified copy of JP 2003-073925 is enclosed with this Amendment.

Since Yamaguchi is not effective as a prior art reference, the rejections of claims 1-6, 11-13, 15, 16, 18 and 19 under 35 USC 102(e) in reliance on Yamaguchi should be withdrawn.

Claim Rejections – 35 USC 102(b) - Nagai

Claims 1 and 11-13 are rejected under 35 USC 102(b) as anticipated by Nagai (US 6,396,145). In response, independent claims 1 and 11 are amended to include the limitations of dependent claim 2, which is not rejected over Nagai and clearly distinguishes claims 1 and 11 over Nagai.

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Nagai discloses a semiconductor device 10 having a wafer substrate 1 with electrode pads 2 formed at a periphery thereof. See Nagai, FIGS. 2a-2f, 4, Col. 11, lines 6-54. A stress relaxation layer 3 of resin is formed so as to overlap a second rim part (inner part) of the electrode pads 2 and to leave out an area from the periphery of the wafer substrate 1 to a first rim part (outer part) of the electrode 2. See Nagai, Col. 7, line 63 to Col. 8, line 2. However, Nagai does not disclose or suggest a passivation film formed on the side of the semiconductor substrate where the electrode is formed, and a resin layer formed on the passivation film, as is required by claims 1 and 11, as amended.

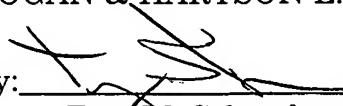
Since Nagai does not disclose each and every limitation of claims 1 and 11, as amended, it cannot anticipate those claims or claims 12 and 13 dependent thereon. The rejections of claims 1 and 11-13 under 35 USC 102(b) should be withdrawn.

Conclusion

This application is now believed to be in condition for allowance. The Examiner is invited to telephone the undersigned to resolve any issues that remain after entry of this amendment. Any fees due with this response may be charged to our Deposit Account No. 50-1314.

Respectfully submitted,
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